

a thin-layer of Si which allows further epitaxial growth;

a p^+ -type Si layer, having addressing contact electrodes;

a thin (about 10 nm) SiO_2 layer deposited and patterned with a pitch of about 0.1 microns;

a n -Si layer forming nanotips;

an n -type wide energy gap layer selected from the group of semiconductors consisting of $\text{Zn}_a\text{Mg}_{1-a}\text{Se}$, $\text{Zn}_a\text{Mg}_{1-a}\text{S}$, $\text{Zn}_a\text{Mg}_{1-a}\text{S}_b\text{S}_{1-b}$, $\text{Zn}_a\text{Be}_{1-a}\text{S}_b\text{S}_{1-b}$, $\text{Al}_c\text{Ga}_{1-c}\text{N}$, ZnMgBeSe , and AlInN , stacked on layer with nanotips;

a layer comprising cladded quantum dots;

a p -type wider energy gap (than said wide p - wide energy gap layer) semiconductors layer selected from the group of semiconductors consisting of: $\text{Zn}_a\text{Mg}_{1-a}\text{Se}$, $\text{Zn}_a\text{Mg}_{1-a}\text{S}$, $\text{Zn}_a\text{Mg}_{1-a}\text{S}_b\text{S}_{1-b}$, $\text{Zn}_a\text{Be}_{1-a}\text{S}_b\text{S}_{1-b}$, $\text{Al}_c\text{Ga}_{1-c}\text{N}$, ZnMgBeSe , and AlInN ; and

a layer forming contact electrodes, wherein said set of electrodes being appropriately biased and addressed to create a two-dimensional display.

Claim 44. (previously amended) The EL device as described in claim 1, wherein the electrodes at the bottom of the device are separated by reverse biased junctions.

REMARKS

Claims 1-3, 11, 13, 22, 38 have been amended. Claims 5-8, 10, 12, 14-16, 18, 20, 25-27, 29 and 39-44 remain as previously amended. The Examiner stated that all these claims "contain allowable subject material" and claim 43 is allowed. This amendment is submitted to overcome the objections and rejections cited by the Examiner as follows:

The Examiner objected to claim 1 for missing a period at the end; to claim 3 for using "are" instead of "is". These objections have been corrected as suggested by the Examiner.

The Examiner rejected claims 1-3, 5-8, 10-16, 18, 20, 22, 25-27, 29, 38, 39-42 and 44 under 35 U.S.C. 112 as being indefinite, citing that:

- a. In claim 1, "said p-type layer" in line 10 is indefinite. A "first" has been inserted before "said p-type layer" to differentiate from the "second p-type layer" four lines later.
- b. In claim 1, there is no antecedent basis for "said wide bandgap layer". "Said second p-type layer" has been inserted to replace "said wide bandgap layer".
- c. In claim 1, line 15, "n-type wide bandgap semiconductor layer" has no antecedent basis. The "n-type" has been moved to the beginning of the same line before "semiconductor layer".

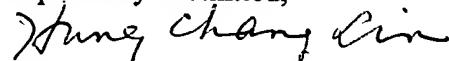
- d. In claim 2, "thin wide energy gap semiconductor" not present in claim 1. "said n-type" has been inserted to replace "thin wide energy gap"
- e. In claim 13, "p-doped wide energy gap semiconductor layer" is not present in claim 1. This phrase has been replaced by "second p-doped semiconductor".
- f. In claim 22, "p-doped wide energy gap semiconductor layer" is not present in claim 1. This phrase has been replaced by "second p-doped semiconductor layer".

With these changes, it is believed that the rejections have been overcome.

In view of the above, it is submitted that claims 1-3, 5-8, 10-16, 18, 20, 22, 25-27, 29 and 38-44 are in condition for allowance. Reexamination of the objections and rejections is requested.

Allowance of these claims at an early is solicited.

Respectfully submitted,



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I hereby certify that this Fee(s) Transmittal is being deposited with the United States Postal Service with sufficient postage for first class mail in an envelope addressed to the Box Issue Fee address above on the date indicated below.

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